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thin Solid films

Contents

Invited Review

Deformation and fracture in microlaminates 1
G.S. Was (Ann Arbor, MI, USA), T. Foecke (Gaithersburg, MD, USA)

Letters

Correlation between the density of TiO_2 films and their properties 32
C.R. Ottermann, K. Bange (Mainz, Germany)

Preparation of ZnO thin films using the flowing liquid film method 35
K. Ito, K. Nakamura (Osaka, Japan)

A new method for preparing nanometer-scale particles onto LB films 37
C. Fan, T. Lu, B. Li, L. Jiang (Beijing, China)

Synthesis and Characterization

Association of some phthalocyanines: from solutions to thin films 40
V.I. Vlaskin, O.P. Dimitriev, Z.I. Kazantseva, A.V. Nabok (Kiev, Ukraine)

Surface roughness of alumina films deposited by reactive r.f. sputtering 45
Y. Zhao, Y. Qian, W. Yu, Z. Chen (Hefei, People's Republic of China)

The structure of Pt–Al_2O_3 composite films prepared by pulsed laser deposition technique 49
Z.G. Liu, X.K. Meng, X.L. Guo, X. Liu, J.M. Liu, J.M. Hong (Nanjing, People's Republic of China)

Studies on the morphology of Al_2O_3 thin films grown by atomic layer epitaxy 54
M. Ritala, H. Saloniemi, M. Leskelä (Helsinki, Finland), T. Prohaska, G. Friedbacher, M. Grasserbauer (Wien, Austria)

Optical characterization of sputtered a-C:H overcoats: relationship to accelerated wear testing, film composition and substrate temperature 59
D.E. Muller, E. Li, V.S. Veerasamy, J. Birkmeyer, J. Ward, J. Weiss (San Jose, CA, USA)

Thin film growth of gadolinia by metal–organic chemical vapour deposition (MOCVD) 64
J. McAleese, J.C. Plakatouras, B.C.H. Steele (London, UK)

Structurally stable composite Pd–Ag alloy membranes: Introduction of a diffusion barrier 72
J. Shu, A. Adnot, B.P.A. Grandjean, S. Kaliaguine (Quebec, Canada)

a-$SiSn_x$:H thin films prepared by ion beam assisted deposition 80
B.G. Goodyear, D.E. Brodie (Waterloo, Ontario, Canada)

Preparation of regularly structured porous metal membranes with two different hole diameters at the two sides 88
P. Hoyer, K. Nishio, H. Masuda (Tokyo, Japan)

Vertical thin-film-edge field emitters: fabrication by chemical beam deposition, imaging of cathodoluminescence and characterization of emission 92
D.S.Y. Hsu, H.F. Gray (Washington DC, USA)

Highly oriented polytetrafluoroethylene films: a force microscopy study 98
P. Bodö, M. Schott (Paris, France)

Characterization of GaAs buffer layer function in GaAs/InP strained structure grown by MBE 107
C.-T. Lee, C.-Y. Wang (Chung-Li, Taiwan, ROC), Y.-C. Chou (Tainan, Taiwan, ROC)

Elsevier Science S.A.

Investigation of the stresses and stress intensity factors responsible for fracture of thin protective films during ultra-micro indentation tests with spherical indenters 111
E. Weppelmann (Freiburg, Germany), M.V. Swain (Lindfield, NSW, Australia)

Plasma-deposited CdS layers from (o-phen)bis(diethyldithiocarbamate) cadmium 122
N.I. Fainer, Yu.M. Rumyantsev, E.G. Salman, M.L. Kosinova, G.S. Yurjev, N.P. Sysoeva, E.A. Maximovskii, S.V. Sysoev, A.N. Golubenko (Novosibirsk, Russia)

Dry and wet corrosion behaviour of AISI 304 stainless steel coated by sol–gel ZrO_2–CeO_2 films 127
R. Di Maggio, L. Fedrizzi, S. Rossi, P. Scardi (Trento, Italy)

Lattice orientation relation of the $AuIn_2$ phase in the alloying process of gold–indium films on mica 136
Y. Kubota, K. Kifune, K. Yamamoto (Osaka, Japan)

Preparation and characterization of lithium metaborate thin films obtained by a sol–gel method 141
N.D. Huy, S. Badilescu, Y. Djaoued, F.E. Girouard, G. Bader, P.V. Ashrit, V.-V. Truong (Moncton, NB, Canada)

Crystallography of epitaxial growth of $Fe_{16}N_2$ single-crystal films on NaCl substrates 146
D.C. Sun (Beijing, China), E.Y. Jiang, C. Lin (Tianjin, China)

Electrodeposition of $CuInS_2$ from aqueous solution (II) Electrodeposition of $CuInS_2$ film 151
T. Yukawa, K. Kuwabara, K. Koumoto (Nagoya, Japan)

Dye-metal oxide composite thin films for decorative applications 154
S. Jäger (Braunschweig, Germany)

Surfaces, Interfaces and Colloidal Behaviour

A model describing the energy distribution of ions bombarding electrodes in an RF-plasma reactor 159
P. Altanzog (Ulaanbaatar, Mongolia), M. Albert, K. Schade (Dresden, Germany)

Air pockets in thin porous platinum films studied by spectroscopic ellipsometry 164
S. Guo, E. Hedborg, I. Lundström, H. Arwin (Linköping, Sweden)

WN_x diffusion barriers between Si and Cu 170
M. Uekubo, T. Oku, K. Nii, M. Murakami (Kyoto, Japan), K. Takahiro, S. Yamaguchi (Sendai, Japan), T. Nakano, T. Ohta (Chiba, Japan)

Interdiffusion in Co/C soft X-ray multilayer mirrors 176
H.L. Bai, E.Y. Jiang, C.D. Wang (Tianjin, China)

Multilayer relaxation features on (100) and (111) surfaces of β-SiC 184
T. Halicioglu (Moffett Field, CA, USA)

Metallurgical, Protective and Hard Layers

LaB_6-based, Zr-alloyed, decorative hard coatings 188
V.-H. Derflinger, W. Waldhauser, C. Mitterer (Leoben, Austria), P. Schmölz, H. Störi (Wien, Austria)

Growth and characterization of Ta/W multiscalar multilayer composite films 196
A.K. Malhotra, S.M. Yalisove, J.C. Bilello (Ann Arbor, MI, USA)

Mechanics and Nanomechanics of Thin Layers

Measurements of the debond energy for thin metallization lines on dielectrics 203
A. Bagchi, A.G. Evans (Cambridge, MA, USA)

Electronics, Optics and Opto-electronics

High temperature tin–copper joints produced at low process temperature for stress reduction 213
C.C. Lee, Y.-C. Chen (Irvine, CA, USA)

RTA and stoichiometry effect on the thermochromism of VO_2 thin films 219
M.-H. Lee, M.-G. Kim (Suwon, South Korea)

Langmuir–Blodgett, Biological and Related Films

Electrical state of the water surface determined by the moving electrode set-up 223
H. Hasmonay, G. Dumas, A. Hochapfel, P. Peretti (Paris, France)

Vacuum vapour deposition of phthalimide and phthalanhydride derivatives on the substrates covered with monolayer films 227
G.K. Zhavnerko, T.A. Kuchuk, V.E. Agabekov (Minsk, Belarus)

Studies on the aggregation behaviour of a side-chain liquid crystalline polymer in Langmuir–Blodgett films 232
X. Chen, Q.-B. Xue, K.-Z. Yang, Q.-Z. Zhang (Jinan, People's Republic of China)

A new azo rare earth coordination compound for second-order non-linear optical Langmuir–Blodgett films 237
L.H. Gao, K.Z. Wang, C.H. Huang, Y.F. Zhou, T.K. Li, J.M. Xu, X.S. Zhao, X.H. Xia (Beijing, People's Republic of China)

Low-temperature plasma treatment of magnesium stearate Langmuir–Blodgett films 241
V. Hessel, P. Detemple, J.F. Geiger, M. Keil, R. Schäfer (Mainz-Hechtsheim, Germany), R. Festag, J.H. Wendorff (Marburg, Germany)

Thin Film Devices, Sensors and Actuators

Properties of insulated gate field-effect transistors with a polyaniline gate electrode 252
M. Liess, D. Chinn, D. Petelenz (Salt Lake City, UT, USA), J. Janata (Richland, WA, USA)

Effects of NO_2 oxidizing gas on a novel phthalocyanine Langmuir–Blodgett thin film 256
R. Rella, A. Serra, P. Siciliano, A. Tepore, L. Valli, A. Zocco (Lecce, Italy)

Electrochemical codeposition of indium and gallium for chalcopyrite solar cells 259
J. Zank, M. Mehlin, H.P. Fritz (Garching, Germany)

Thermal stability of metallized CVD diamond 264
C.D. Iacovangelo (Schenectady, NY, USA)

Fabrication of $La_{1-x}Sr_xFe_{1-y}Co_yO_3$ sensitive ceramics, nanocrystalline thin films and the manufacture of the NCTF-OSFET gas sensing device 270
Z. Peng, X. Li, M. Zhao, H. Cai, S. Zhao, G. Hu, B. Xu (Changchun, People's Republic of China)

Recent developments in RF sputtered cadmium stannate films 274
X. Wu, W.P. Mulligan, T.J. Coutts (Golden, CO, USA)

Transport properties in oxygen-doped cobalt phthalocyanine thin film devices 277
T.G. Abdel-Malik, R.M. Abdel-Latif (Minia, Egypt)

Condensed Matter Film Behaviour

Surface and buried-interfacial reactivity of iron and MoS_2: a study of laser-deposited materials 282
T.-S. Lee, B. Esposito (Auburn, AL, USA), M.S. Donley, J.S. Zabinski (OH, USA), B.J. Tatarchuk (Auburn, AL, USA)

Effect of halide ions on the formation and dissolution behaviour of zirconium oxide 289
G.A. EL-Mahdy (Beni-Seuf, Egypt), S.S. Mahmoud (Cairo, Egypt), H.A. El-Dahan (Dokki, Egypt)

The observation of Co film oxidation on Si and SiO_2 substrates 295
Z.L. Zhang, Z.G. Xiao, G.W. Tu (Beijing, China)

Electrical passivation of B-doped Si through thin films used in VLSI fabrication 299
K. Tsukamoto, S. Iwasaki, T. Sadoh, Y. Kuroki (Fukuoka, Japan)

Numerical simulation of the characteristics of the different metallic species falling on the growing film in d.c. magnetron sputtering 305
A. Malaurie, A. Bessaudou (Limoges, France)

Grain boundary enhanced oxygen out-diffusion in annealed polycrystalline Si/SiO_2/crystalline Si structures 317
R.A.B. Devine, D. Mathiot (Meylan, France), J.-B. Xu, I.H. Wilson (Hong Kong, Hong Kong), M. Gauneau (Lannion, France), W.L. Warren (Albuquerque, NM, USA)

High-resolution electron energy loss spectroscopy of thin crystalline highly oriented films of poly(tetrafluoroethylene) 321
P. Dannetun, M. Schott (Paris, France), M. Rei Vilar (Thiais, France)

Rh particle growth on insulator substrates: RHEED study 330
K. Mašek, V. Matolín (Prague, Czech Republic)

Author Index of Volume 286 337

Subject Index of Volume 286 339

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